

Silicon NPN Power Transistors

2SC1343

DESCRIPTION

- With TO-3 package
- Wide area of safe operation

APPLICATIONS

- For audio frequency power amplifier applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

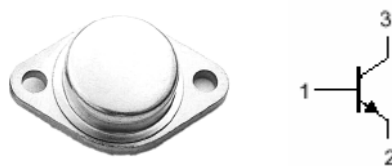


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings($T_a = \square$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	150	V
V_{CEO}	Collector-emitter voltage	Open base	110	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		10	A
P_C	Collector power dissipation	$T_C = 25 \square$	100	W
T_j	Junction temperature		150	$\square$
T_{stg}	Storage temperature		-55~150	$\square$

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CHARACTERISTICS

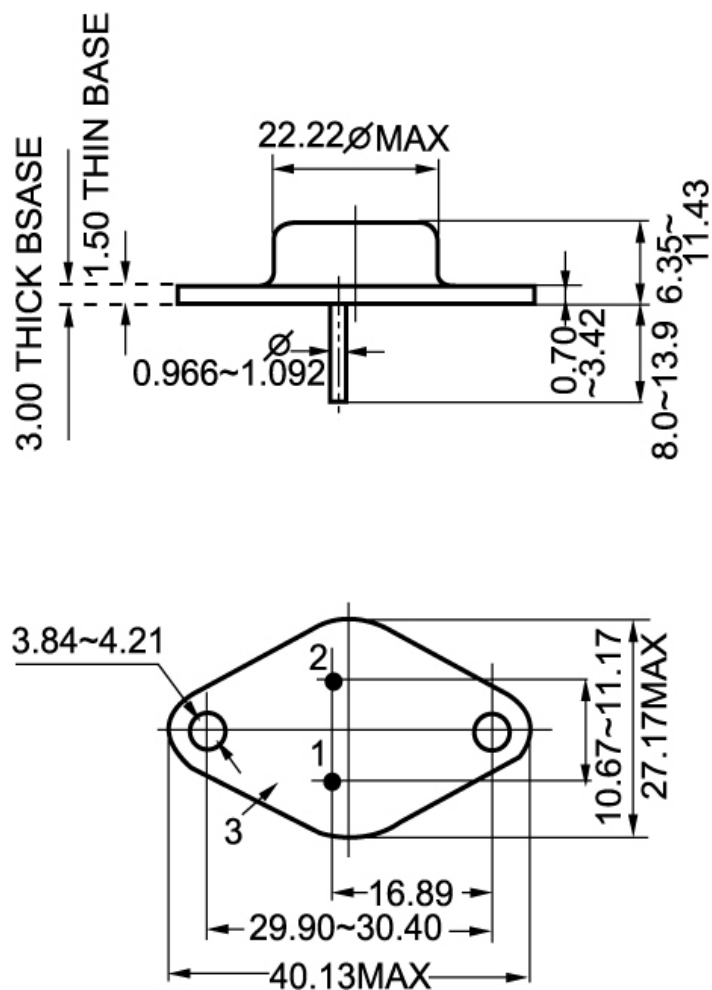
Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=50mA ; I_B=0$	110			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1mA ; I_C=0$	5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=5A ; I_B=0.5A$			2.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=5A ; I_B=0.5A$			2.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=150V ; I_E=0$			0.1	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V ; I_C=0$			0.1	mA
h_{FE-1}	DC current gain	$I_C=1A ; V_{CE}=5V$	30		200	
h_{FE-2}	DC current gain	$I_C=5A ; V_{CE}=5V$	20			
f_T	Transition frequency	$I_C=1A ; V_{CE}=5V$		14		MHz

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PACKAGE OUTLINE

Fig.2 outline dimensions (unindicated tolerance: $\pm 0.1\text{mm}$)